

Features

- Trench Power LV MOSFET Technology
- High Density Cell Design for Low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

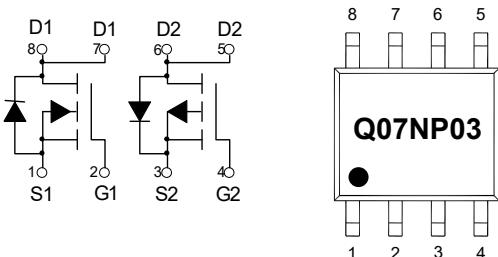
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 78°C/W Junction to Ambient (Note2)

Parameter	Symbol	Rating	Unit
Total Power Dissipation (Note3)	P_D	1.6	W
N-Channel			
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_A=25^\circ C$	I_D	7	A
$T_A=70^\circ C$		5.6	
Pulsed Drain Current (Note4)	I_{DM}	28	A
P-Channel			
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_A=25^\circ C$	I_D	-7	A
$T_A=70^\circ C$		-5.6	
Pulsed Drain Current (Note4)	I_{DM}	-28	A

Note:

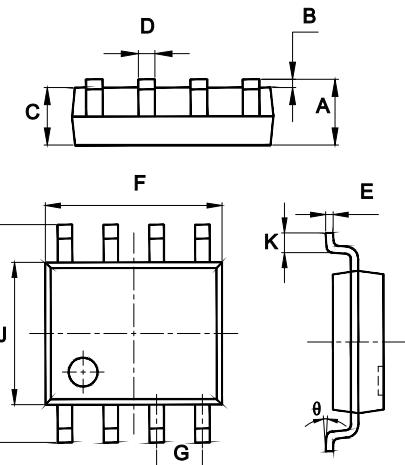
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{thJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. copper, in a still air environment with $T_A=25^\circ C$.
3. P_D is based on max. junction temperature, using junction-ambient thermal resistance.
4. Repetitive rating; pulse width limited by max. junction temperature.

Internal Structure and Marking Code



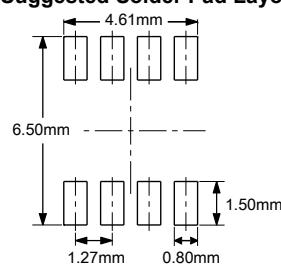
Dual N&P-Channel MOSFET

SOP-8



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.053	0.069	1.35	1.75	
B	0.004	0.010	0.10	0.25	
C	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
H	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.050	0.40	1.27	
θ	0°	8°	0°	8°	

Suggested Solder Pad Layout



N-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.2	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6A$		15	18	$m\Omega$
		$V_{GS}=4.5V, I_D=5A$		23	30	
Gate Resistance	R_G	f=1MHz, Open drain		1.7		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				7	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=6A$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F=5.6A, dI_F/dt=100A/\mu s$		11		ns
Reverse Recovery Charge	Q_{rr}			3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		357		pF
Output Capacitance	C_{oss}			70		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V, I_D=5.6A$		8.5		nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=3\Omega, I_D=5.6A$		5		ns
Turn-On Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			12		
Turn-Off Fall Time	t_f			3		

P-Channel Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-6A$		17	23	$m\Omega$
		$V_{GS}=-4.5V, I_D=-5A$		22	34	
Gate Resistance	R_G	f=1MHz, Open drain		10		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-7	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-6A$			-1.2	V
Reverse Recovery Time	t_{rr}	$I_F=-7.5A, dI_F/dt=100A/\mu s$		18		ns
Reverse Recovery Charge	Q_{rr}			8		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		1623		pF
Output Capacitance	C_{oss}			188		
Reverse Transfer Capacitance	C_{rss}			165		
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-10V, I_D=-9A$		31		nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			5.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-15V, V_{GS}=-10V, R_G=2.5\Omega, I_D=-7.5A$		9		ns
Turn-On Rise Time	t_r			13		
Turn-Off Delay Time	$t_{d(off)}$			54		
Turn-Off Fall Time	t_f			25		

N-Channel MOSFET Curve Characteristics

Fig.1 - Typical Output Characteristics

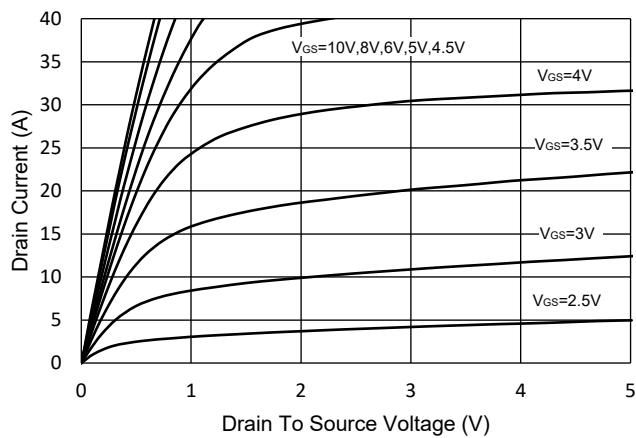


Fig.2 - Transfer Characteristic

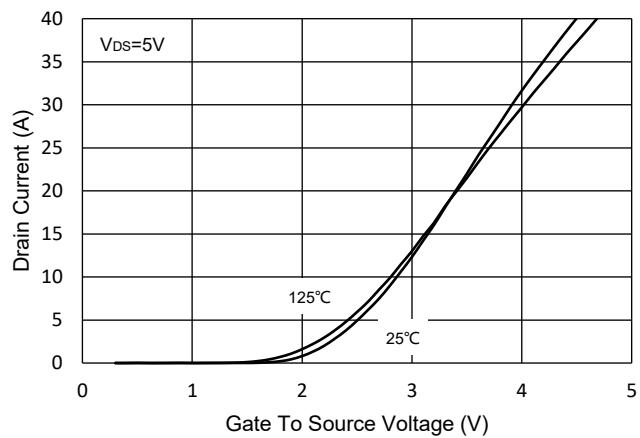


Fig.3 - $R_{DS(ON)}$ - V_{GS}

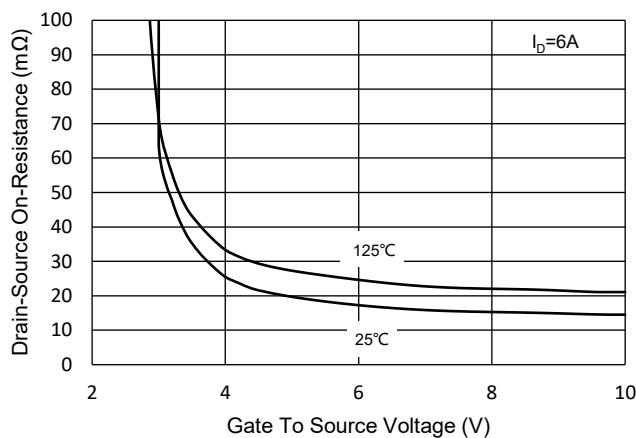


Fig.4 - $R_{DS(ON)}$ - I_D

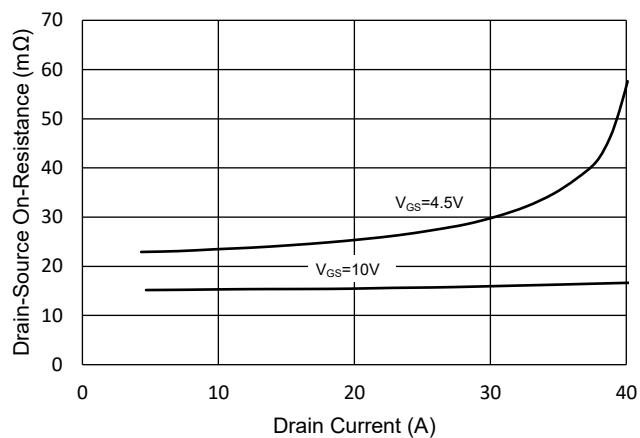


Fig.5 - Capacitance Characteristics

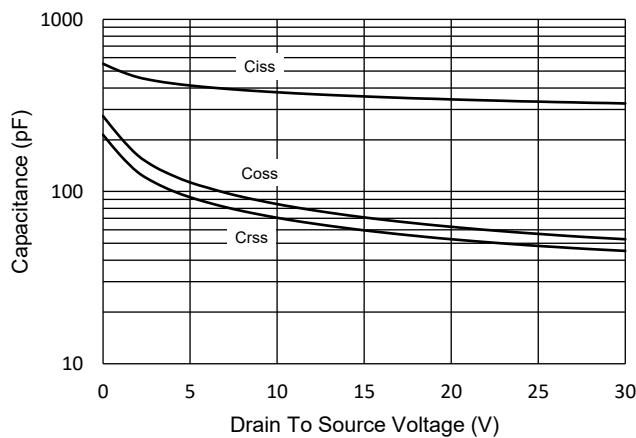
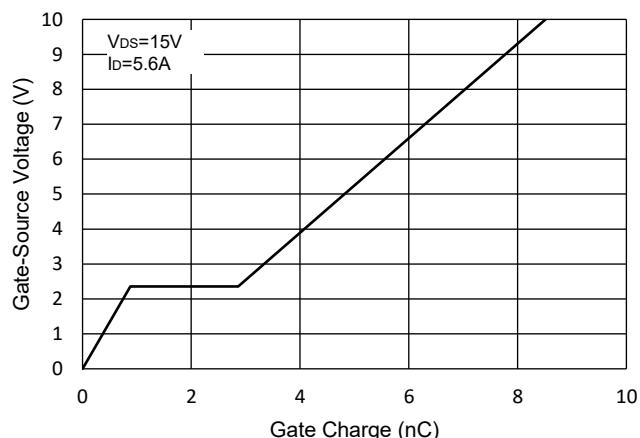


Fig.6 - Gate Charge



N-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

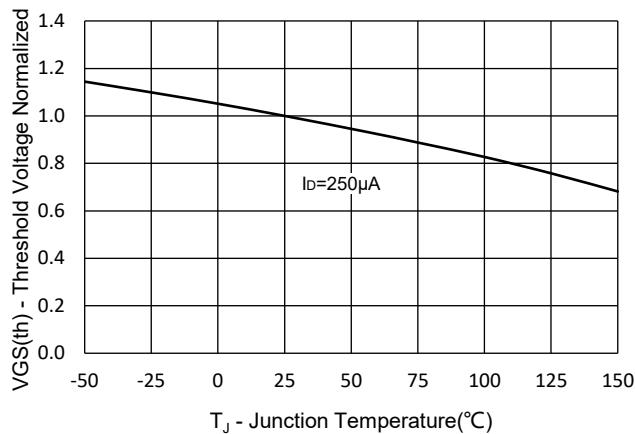


Fig.8 - Normalized On Resistance Characteristics

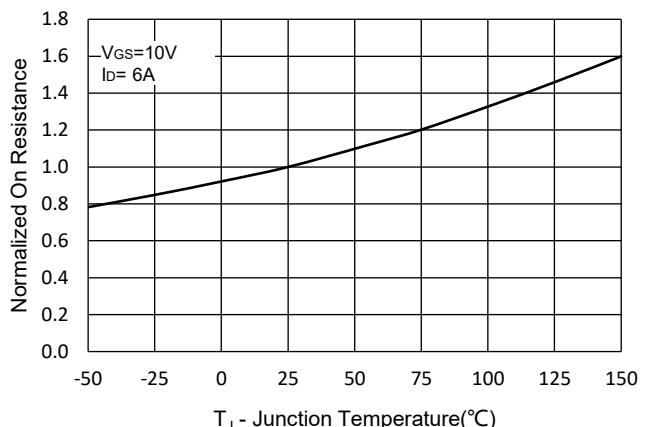


Fig.9 - I_s - V_{SD}

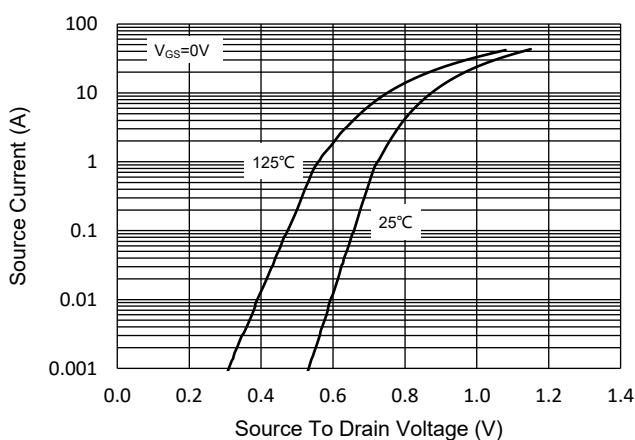


Fig.10 - Drain Current

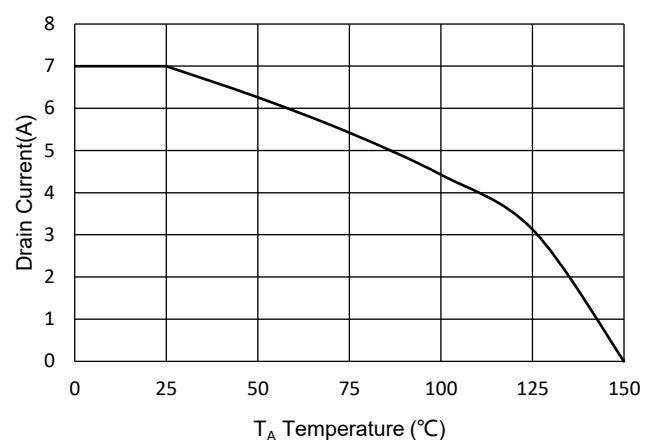
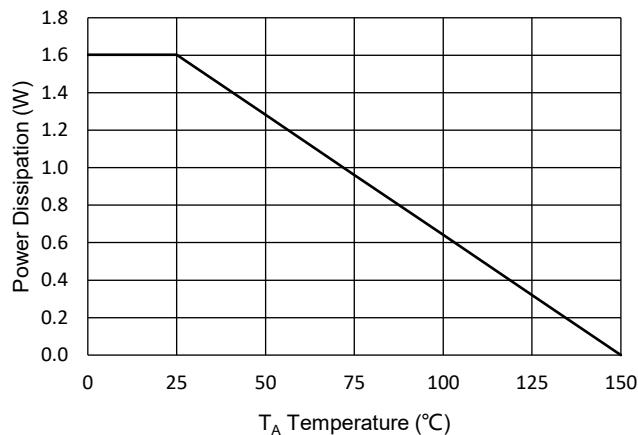


Fig.11 - PD Dissipation



N-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

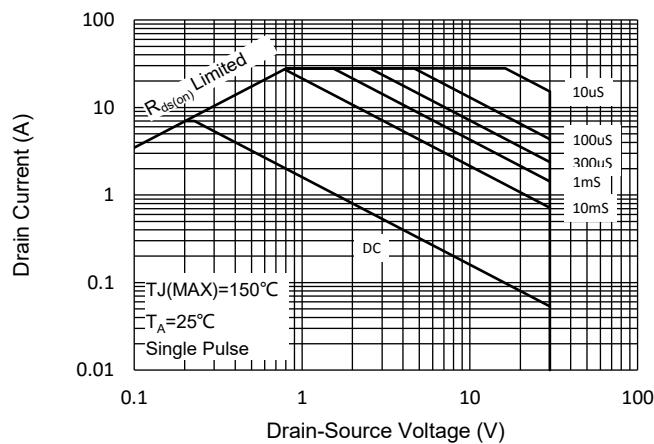
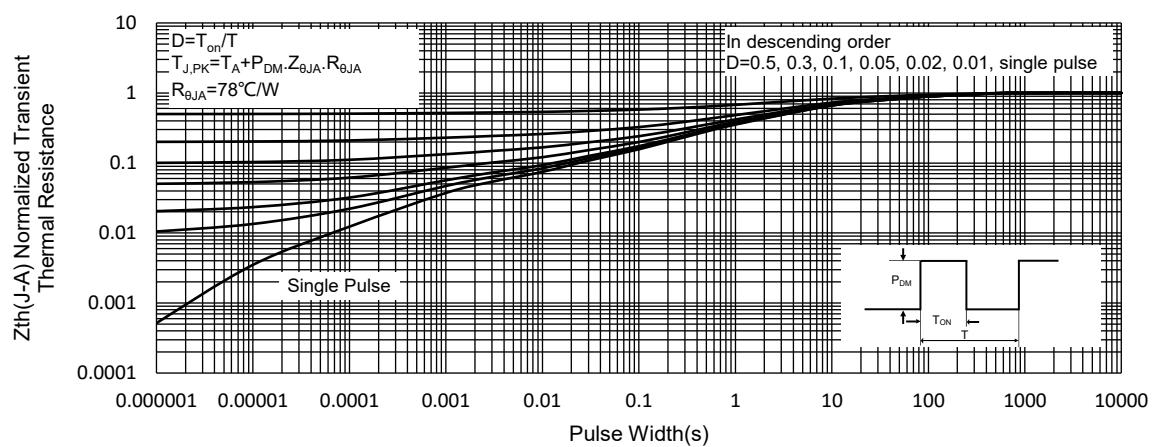


Fig.13 - Normalized Transient Thermal Impedance



P-Channel MOSFET Curve Characteristics

Fig.1 - Typical Output Characteristics

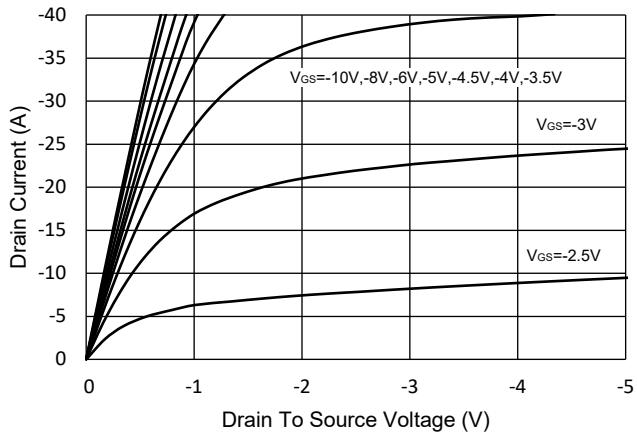


Fig.2 - Transfer Characteristic

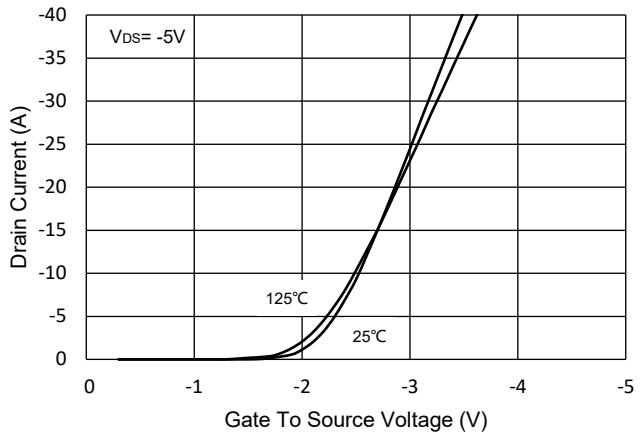


Fig.3 - $R_{DS(ON)}$ - V_{GS}

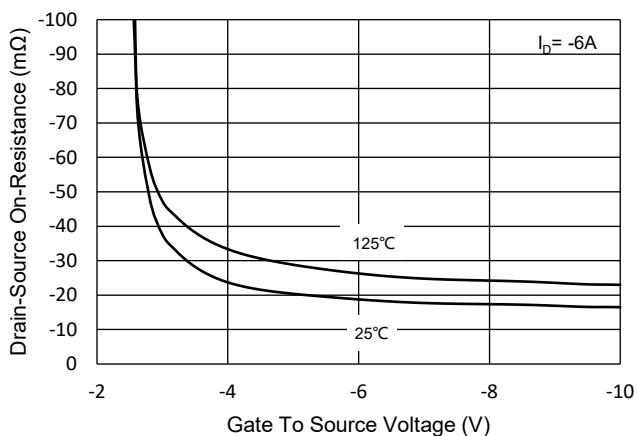


Fig.4 - $R_{DS(ON)}$ - I_D

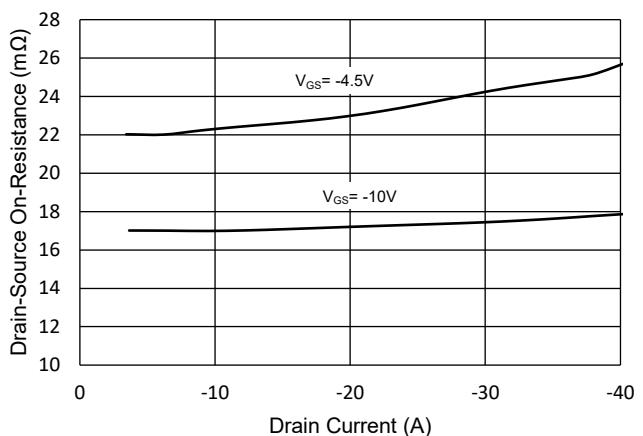


Fig.5 - Capacitance Characteristics

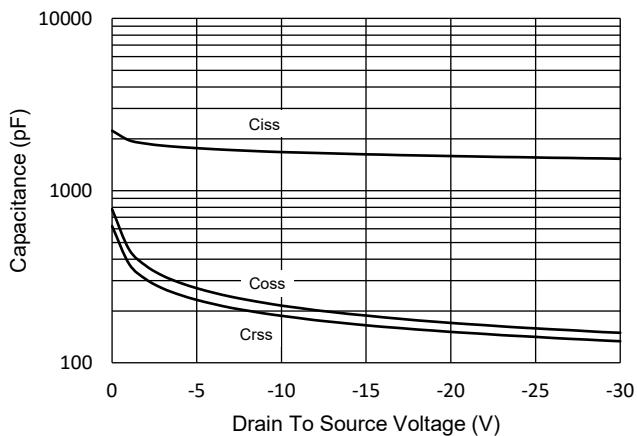
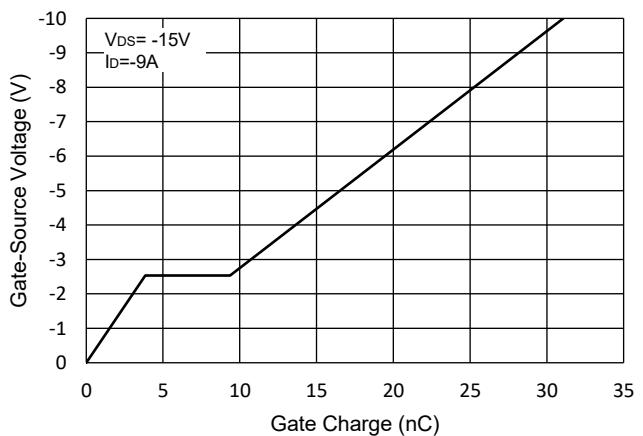


Fig.6 - Gate Charge



P-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

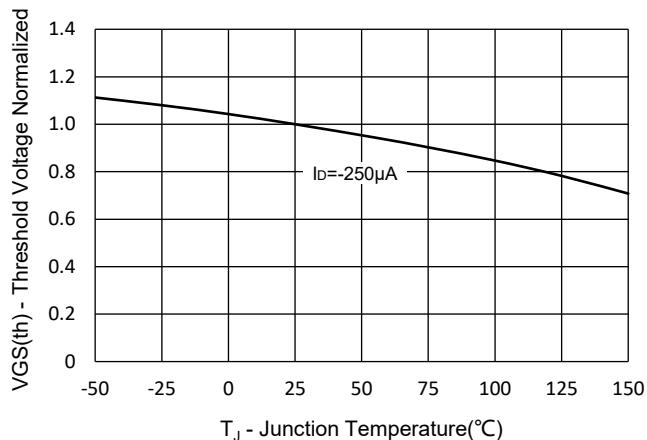


Fig.8 - Normalized On Resistance Characteristics

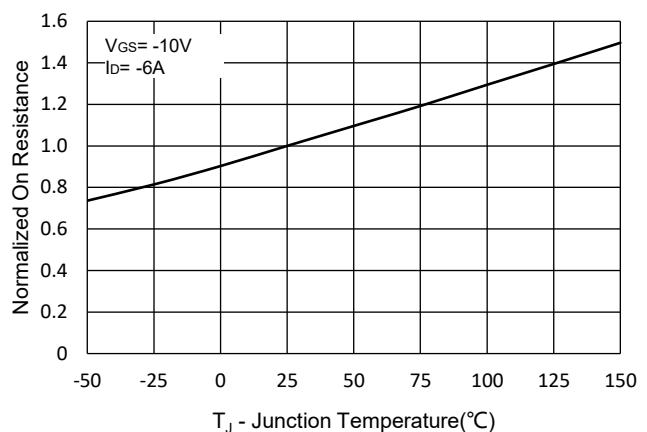


Fig.9 - I_S - V_{SD}

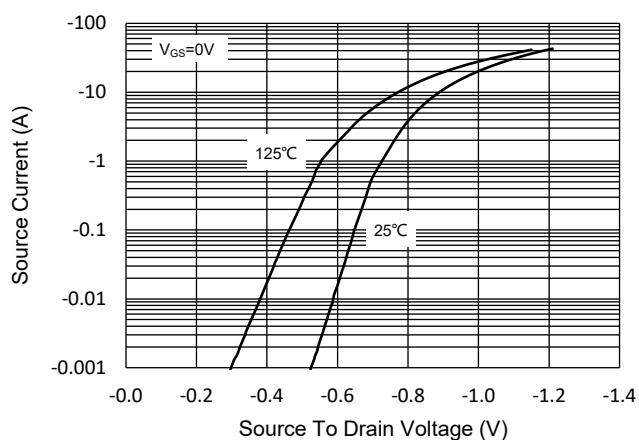


Fig.10 - Drain Current

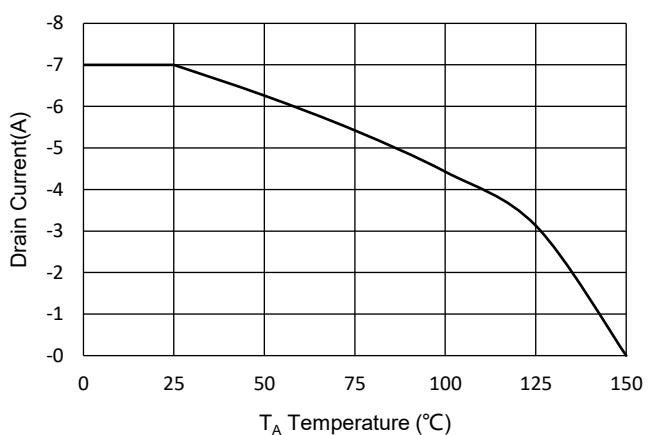
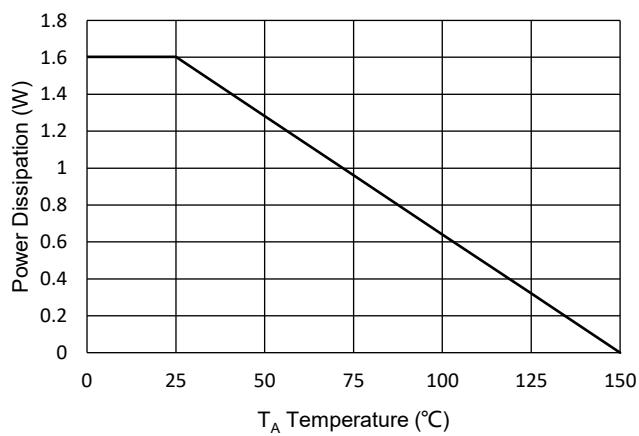


Fig.11 - PD Dissipation



P-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

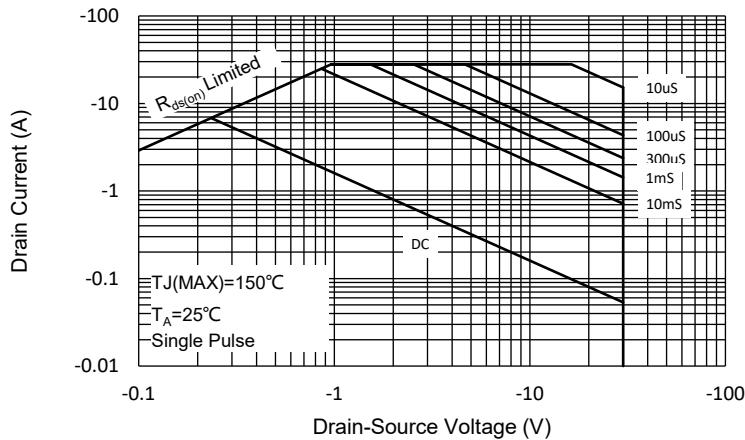
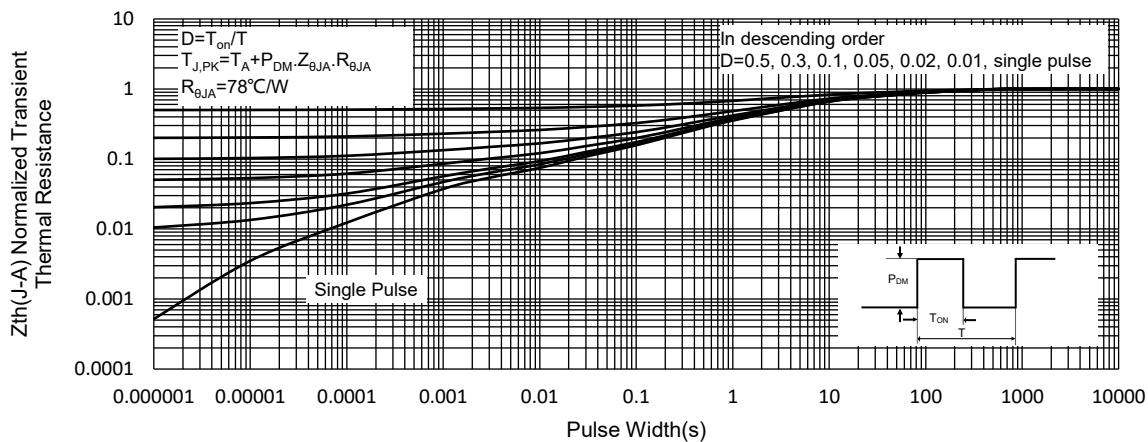


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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